DUSEU

6-Pin DIP General Purpose Photodarlington Optocoupler

4N29M, 4N30M, 4N32M, 4N33M, H11B1M, TIL113M

Description

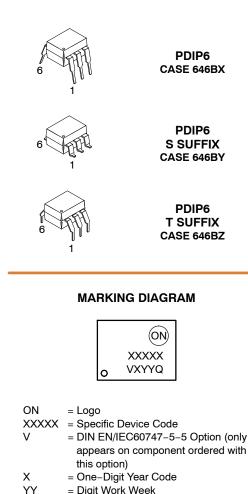
The 4N29M, 4N30M, 4N32M, 4N33M, H11B1M, and TIL113M have a gallium arsenide infrared emitter optically coupled to a silicon planar photodarlington.

Features

- High Sensitivity to Low Input Drive Current
- Meets or Exceeds All JEDEC Registered Specifications
- Safety and Regulatory Approvals:
 - ◆ UL1577, 4,170 VAC_{RMS} for 1 Minute
 - DIN-EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage

Applications

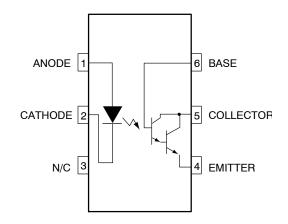
- Low Power Logic Circuits
- Telecommunications Equipment
- Portable Electronics
- Solid State Relays
- Interfacing Coupling Systems of Different Potentials and Impedances



= Digit Work Week Q

= Assembly Package Code

SCHEMATIC



ORDERING INFORMATION

See detailed ordering and shipping information on page 8 of this data sheet.

SAFETY AND INSULATION RATINGS (As per DIN EN/IEC 60747–5–5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.)

Parameter		Characteristics	
Installation Classifications per DIN VDE 0110/1.89 Table 1,	<150 V _{RMS}	I–IV	
For Rated Mains Voltage	<300 V _{RMS}	I–IV	
Climatic Classification	55/100/21		
Pollution Degree (DIN VDE 0110/1.89)	2		
Comparative Tracking Index		175	

Symbol	Parameter	Value	Unit
V _{PR}	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	1360	V _{peak}
	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC	1594	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	850	V _{peak}
VIOTM	Highest Allowable Over-Voltage	6000	V _{peak}
	External Creepage	≥7	mm
	External Clearance	≥7	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥0.5	mm
Τ _S	Case Temperature (Note 1)	175	°C
I _{S,INPUT}	Input Current (Note 1)	350	mA
P _{S,OUTPUT}	Output Power (Note 1)	800	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V (Note 1)	>10 ⁹	Ω

1. Safety limit values - maximum values allowed in the event of a failure.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
OTAL DEV	ICE	• •	
T _{STG}	Storage Temperature	-40 to +125	°C
T _{OPR}	Operating Temperature	-40 to +100	°C
TJ	Junction Temperature	-40 to +125	°C
T _{SOL}	Lead Solder Temperature	260 for 10 seconds	°C
PD	Total Device Power Dissipation @ T _A = 25°C	270	mW
	Derate Above 25°C	3.3	mW/°C
MITTER			
١ _F	Continuous Forward Current	80	mA
V _R	Reverse Voltage	3	V
IF ^(pk)	Forward Current – Peak (300 µs, 2% Duty Cycle)	3.0	А
PD	LED Power Dissipation @ $T_A = 25^{\circ}C$	120	mW
	Derate Above 25°C	2.0	mW/°C
ETECTOR	·		
D) (

BV _{CEO}	Collector-Emitter Breakdown Voltage	30	V
BV _{CBO}	3V _{CBO} Collector-Base Breakdown Voltage		V
BV _{ECO}	Emitter-Collector Breakdown Voltage	5	V
PD	Detector Power Dissipation @ $T_A = 25^{\circ}C$	150	mW
	Derate Above 25°C	2.0	mW/°C
۱ _C	Continuous Collector Current	150	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS - INDIVIDUAL COMPONENT CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Symbol	Parameter	Test Conditions	Device	Min	Тур	Max	Unit
EMITTER							
V _F	Input Forward Voltage (Note 2)	I _F = 10 mA	4NXXM	-	1.2	1.5	V
			H11B1M, TIL113M	0.8	1.2	1.5	V
I _R	Reverse Leakage Current (Note 2)	V _R = 3.0 V	4NXXM	-	0.001	100	μA
		VR = 6.0 V	H11B1M, TIL113M	-	0.001	10	μΑ
С	Capacitance (Note 2)	V _F = 0 V, f = 1.0 MHz	All	-	150	-	pF
DETENTOR							

DETECTOR

BV _{CEO}	Collector-Emitter Breakdown Voltage (Note 2)	I _C = 1.0 mA, I _B = 0	4NXXM, TIL113M	30	60	-	V
			H11B1M	25	60	-	V
BV _{CBO}	Collector-Base Breakdown Voltage (Note 2)	$I_{C} = 100 \ \mu A, \ I_{E} = 0$	All	30	100	-	V
BV _{ECO}	Emitter-Collector Breakdown Voltage	I _E = 100 μA, I _B = 0	4NXXM	5.0	10	-	V
	(Note 2)		H11B1M, TIL113M	7	10	-	V
I _{CEO}	Collector-Emitter Dark Current (Note 2)	V _{CE} = 10 V, Base Open	All	-	1	100	nA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Indicates JEDEC registered data.

ELECTRICAL CHARACTERISTICS - TRANSFER CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Device	Min	Тур	Max	Unit	
DC CHARAC	DC CHARACTERISTICS							
I _{C(CTR)}	Collector Output Current (Note 3) (Note 4) (Note 5)	$I_{\rm F}$ = 10 mA, V _{CE} = 10 V, $I_{\rm B}$ = 0	4N32M, 4N33M	50 (500)	-	-	mA (%)	
			4N29M, 4N30M	10 (100)	-	-	mA (%)	
		I _F = 1 mA, V _{CE} = 5 V	H11B1M	5 (500)	-	-	mA (%)	
		I _F = 10 mA, V _{CE} = 1 V	TIL113M	30 (300)	-	-	mA (%)	
V _{CE (SAT)}	Saturation Voltage (Note 3) (Note 5)	I _F = 8 mA, I _C = 2.0 mA	4NXXM	-	-	1.0	V	
			TIL113M	-	-	1.25	V	
		I _F = 1 mA, I _C = 1 mA	H11B1M	-	-	1.0	V	

AC CHARACTERISTIC

				-		-	
t _{ON}	Turn-on Time	$\label{eq:lensergy} \begin{array}{l} I_F = 200 \text{ mA}, \ I_C = 50 \text{ mA}, \\ V_{CC} = 10 \text{ V}, \ R_L = 100 \ \Omega \end{array}$	4NXXM, TIL113M	-	-	5.0	μs
		$\begin{array}{l} I_{F} = 10 \text{ mA}, \text{ V}_{CE} = 10 \text{ V}, \\ R_{L} = 100 \ \Omega \end{array}$	H11B1M	-	25	-	μs
t _{OFF}	Turn-off Time	$I_{F} = 200 \text{ mA}, I_{C} = 50 \text{ mA}, \\ V_{CC} = 10 \text{ V}, \text{ R}_{L} = 100 \Omega$	4N32M, 4N33M, TIL113M	-	-	100	μs
			4N29M, 4N30M	-	-	40	μs
		$\begin{array}{l} I_{\text{F}} = 10 \text{ mA}, \text{ V}_{\text{CE}} = 10 \text{ V}, \\ \text{R}_{\text{L}} = 100 \ \Omega \end{array}$	H11B1M	-	18	-	μs
BW	Bandwidth (Note 6) (Note 7)			-	30	-	kHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Indicates JEDEC registered data.

4. The current transfer ratio(I_C/I_F) is the ratio of the detector collector current to the LED input current.

5. Pulse test: pulse width = 300 μ s, duty cycle \leq 2.0%.

6. I_F adjusted to I_C = 2.0 mA and I_C = 0.7 mA rms.

7. The frequency at which I_C is 3 dB down from the 1 kHz value.

$\label{eq:constraint} \textbf{ELECTRICAL CHARACTERISTICS} - \textbf{ISOLATION CHARACTERISTICS} \ (T_A = 25^{\circ}C \ \text{unless otherwise noted})$

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V _{ISO}	Input-Output Isolation Voltage	t = 1 Minute	4170	-	-	VAC _{RMS}
C _{ISO}	Isolation Capacitance	V _{I-O} = 0 V, f = 1 MHz	-	0.2	-	pF
R _{ISO}	Isolation Resistance	$V_{I-O}=\pm 500 \text{ VDC}, T_A=25^\circ \text{C}$	10 ¹¹	-	-	Ω

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL PERFORMANCE CURVES

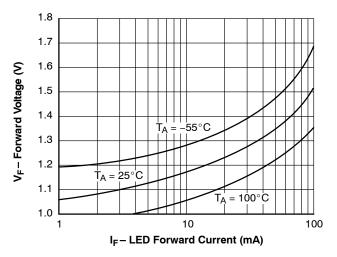


Figure 1. LED Forward Voltage vs. Forward Current

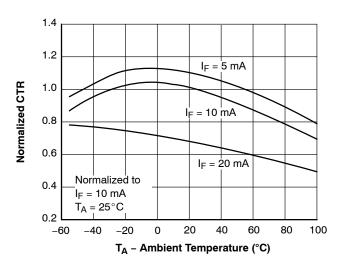


Figure 3. Normalized CTR vs. Ambient Temperature

 $V_{CE} = 0.3$

 $I_F = 5 \text{ mA}$

 $I_F = 10 \text{ mA}$

1.0 0.9

0.8

0.7

0.6

0.5

0.4 0.3

0.2

0.1

0.0

10

(CTR_{RBE} / CTR_{RBE}(OPEN))

Normalized CTR

 $I_F = 20' mA$

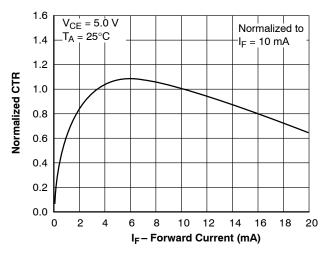


Figure 2. Normalized CTR vs. Forward Current

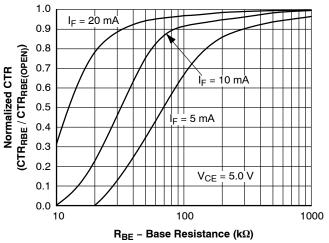


Figure 4. CTR vs. RBE (Unsaturated)

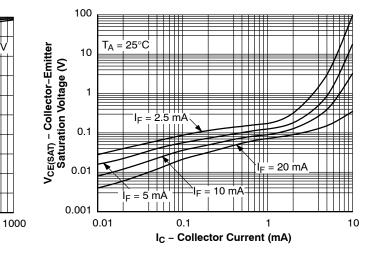


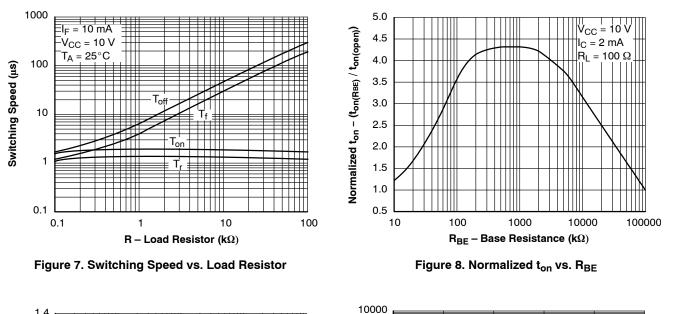
Figure 5. CTR vs. RBE (Saturated)

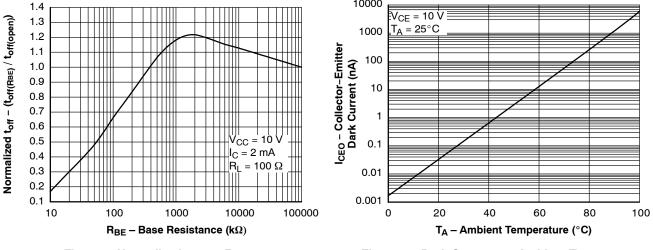
100

R_{BE} – Base Resistance (kΩ)

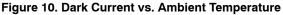


TYPICAL PERFORMANCE CURVES (continued)

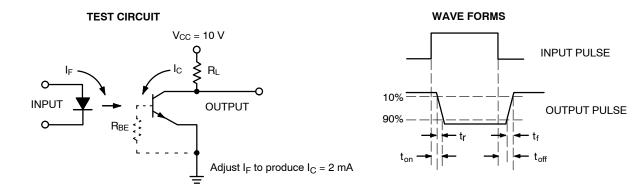






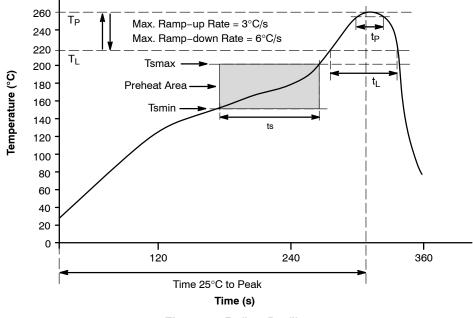


SWITCHING TIME TEST CIRCUIT AND WAVEFORMS





REFLOW PROFILE





REFLOW PROFILE

Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t _S) from (Tsmin to Tsmax)	60–120 s
Ramp-up Rate (t _L to t _P)	3°C/s max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60–150 s
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 s
Ramp-down Rate (T _P to T _L)	6°C/s max.
Time 25°C to Peak Temperature	8 min max.

ORDERING INFORMATION

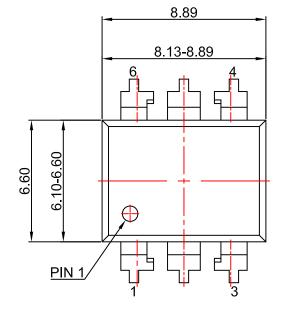
Part Number	Package	Packing Method [†]
4N29M	DIP 6-Pin	50 Units / Tube
4N29SM	SMT 6-Pin (Lead Bend)	50 Units / Tube
4N29SR2M	SMT 6-Pin (Lead Bend)	1000 / Tape & Reel
4N29VM	DIP 6-Pin, DIN EN/IEC60747-5-5 Option	50 Units / Tube
4N29SVM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	50 Units / Tube
4N29SR2VM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	1000 / Tape & Reel
4N29TVM	DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option	50 Units / Tube

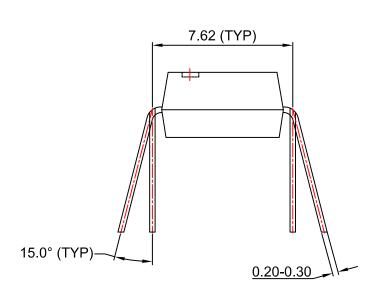
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. 8. The product orderable part number system listed in this table also applies to the 4N30M, 4N32M, 4N33M, H11B1M and TIL113M devices.

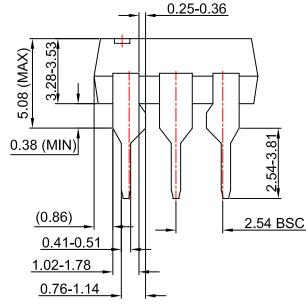


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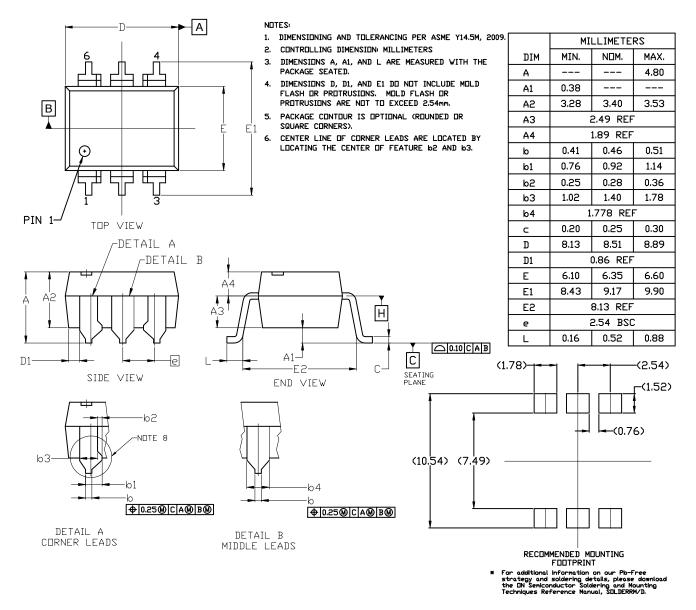
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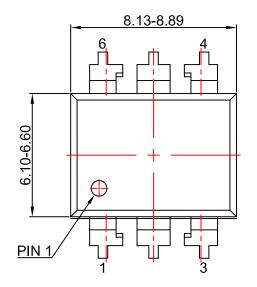


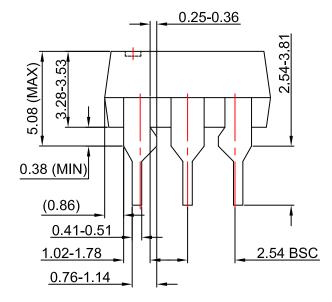
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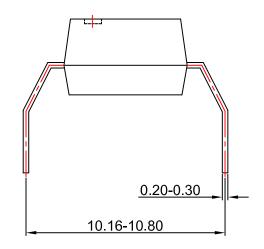


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